

Normally – OFF Silicon Carbide Super Junction Transistor

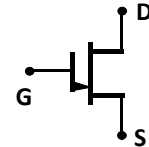
V_{DS}	=	650 V
I_D	=	7 A
$R_{DS(ON)}$	=	170 mΩ

Features

- 250 °C maximum operating temperature
- Temperature independent switching performance
- Gate oxide free SiC switch
- Suitable for connecting an anti-parallel diode
- Positive temperature coefficient for easy paralleling
- Low gate charge
- Low intrinsic capacitance

Package

- RoHS Compliant



TO – 257 (Hermetic Package)

Advantages

- Low switching losses
- Higher efficiency
- High temperature operation
- High short circuit withstand capability

Applications

- Ideal for Aerospace and Defense Applications
- Down Hole Oil Drilling, Geothermal Instrumentation
- Hybrid Electric Vehicles (HEV)
- Solar Inverters
- Switched-Mode Power Supply (SMPS)
- Power Factor Correction (PFC)
- Induction Heating
- Uninterruptible Power Supply (UPS)
- Motor Drives

Maximum Ratings at $T_j = 250\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Drain – Source Voltage	V_{DS}	$V_{GS} = 0\text{ V}$	650	V
Continuous Drain Current	I_D	$T_C = 158\text{ °C}$	7	A
Gate Peak Current	I_{GM}		5	A
Reverse Gate – Source Voltage	V_{GS}		200	V
Reverse Drain – Source Voltage	V_{DS}		40	V
Power Dissipation	P_{tot}	$T_C = 25\text{ °C}$	8	W
Operating and Storage Temperature	T_j, T_{stg}		-55 to 250	°C

Electrical Characteristics at $T_j = 250\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
On Characteristics						
Drain – Source On Voltage	$V_{DS(ON)}$	$I_D = 7\text{ A}, I_G = 250\text{ mA}, T_j = 25\text{ °C}$		1.2		V
		$I_D = 7\text{ A}, I_G = 500\text{ mA}, T_j = 175\text{ °C}$		2.2		
		$I_D = 7\text{ A}, I_G = 500\text{ mA}, T_j = 250\text{ °C}$		3.1		
Drain – Source On Resistance	$R_{DS(ON)}$	$I_D = 7\text{ A}, I_G = 250\text{ mA}, T_j = 25\text{ °C}$		170		mΩ
		$I_D = 7\text{ A}, I_G = 500\text{ mA}, T_j = 175\text{ °C}$		330		
		$I_D = 7\text{ A}, I_G = 500\text{ mA}, T_j = 250\text{ °C}$		550		
Gate Forward Voltage	$V_{GS(FWD)}$	$I_G = 500\text{ mA}, T_j = 25\text{ °C}$		3		V
DC Current Gain	β	$V_{DS} = 5\text{ V}, I_D = 10\text{ A}, T_j = 25\text{ °C}$		120		
		$V_{DS} = 5\text{ V}, I_D = 10\text{ A}, T_j = 250\text{ °C}$		80		

Off Characteristics

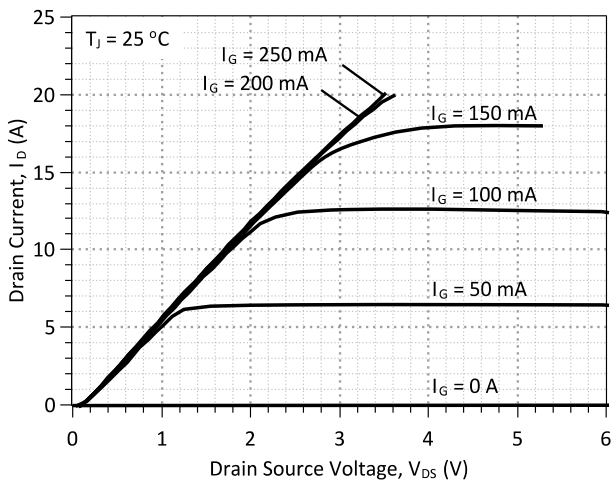
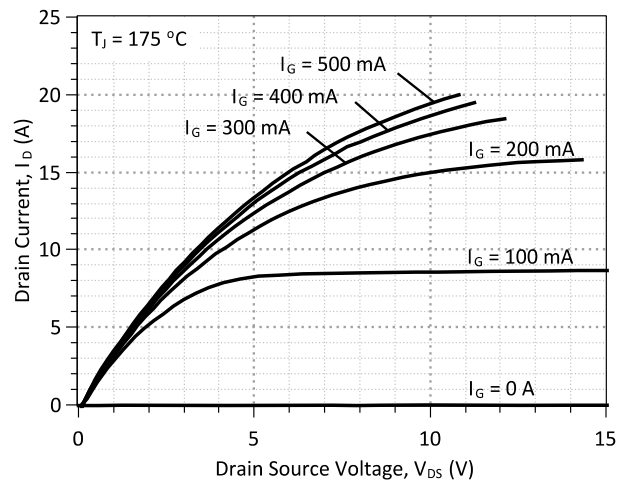
Drain Leakage Current	I_{DSS}	$V_R = 650\text{ V}, V_{GS} = 0\text{ V}, T_j = 25\text{ °C}$	2.5	μA
		$V_R = 650\text{ V}, V_{GS} = 0\text{ V}, T_j = 175\text{ °C}$	4	
		$V_R = 650\text{ V}, V_{GS} = 0\text{ V}, T_j = 250\text{ °C}$	10	

Electrical Characteristics at $T_j = 250\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 35\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}, T_{vj} = 25\text{ }^\circ\text{C}$		720		pF
Output Capacitance	C_{oss}			88		pF
Reverse Transfer Capacitance	C_{rss}			88		pF
Switching Characteristics						
Turn On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 10\text{ A},$ $R_{G(on)} = R_{G(off)} = 32\ \Omega,$ $V_{GS} = -8/15\text{ V}, T_j = 175\text{ }^\circ\text{C}$ Refer to Figure 10 for gate drive current waveforms		11		ns
Rise Time	t_r			28		ns
Turn Off Delay Time	$t_{d(off)}$			76		ns
Fall Time	t_f			38		ns
Turn-On Energy Per Pulse	E_{on}			34		μJ
Turn-Off Energy Per Pulse	E_{off}			64		μJ
Total Switching Energy	E_{ts}		98		μJ	
Turn On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 10\text{ A},$ $R_{G(on)} = R_{G(off)} = 32\ \Omega,$ $V_{GS} = -8/15\text{ V}, T_j = 250\text{ }^\circ\text{C}$ Refer to Figure 10 for gate drive current waveforms		12		ns
Rise Time	t_r			30		ns
Turn Off Delay Time	$t_{d(off)}$			73		ns
Fall Time	t_f			58		ns
Turn-On Energy Per Pulse	E_{on}			43		μJ
Turn-Off Energy Per Pulse	E_{off}			82		μJ
Total Switching Energy	E_{ts}		125		μJ	

Thermal Characteristics

Thermal resistance, junction - case	$R_{th(jc)}$	2.5	$^\circ\text{C/W}$
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Figure 1: Typical Output Characteristics at 25 °C

Figure 2: Typical Output Characteristics at 175 °C

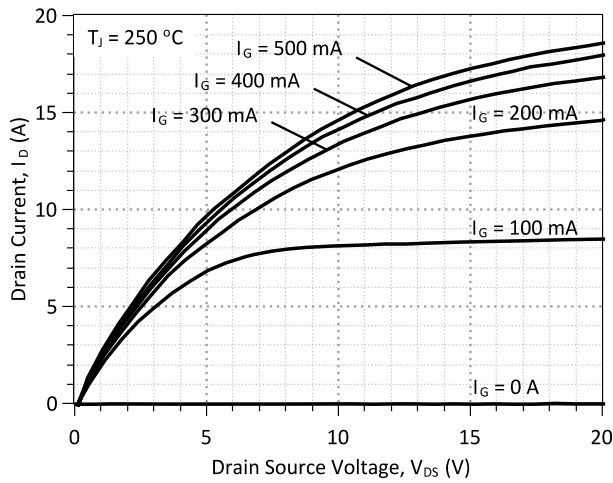


Figure 3: Typical Output Characteristics at 250 °C

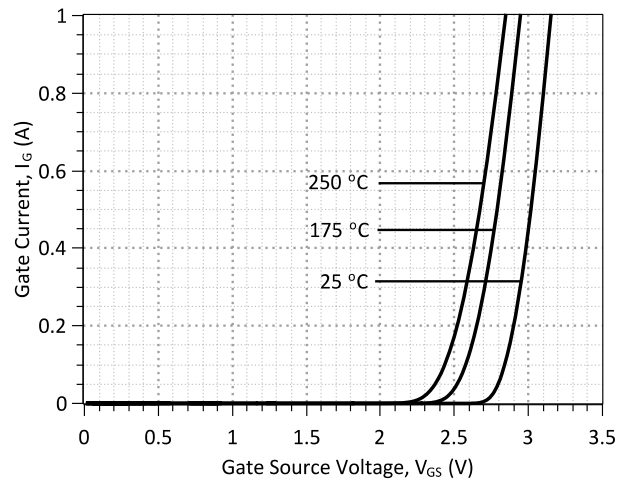


Figure 4: Typical Gate Source I-V Characteristics vs. Temperature

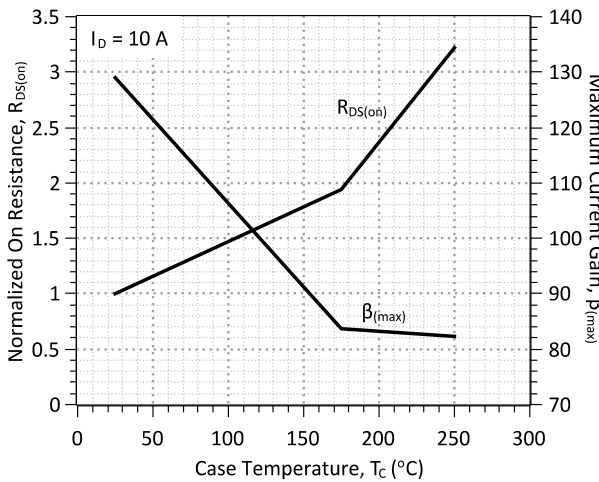


Figure 5: Normalized On-Resistance and Current Gain vs. Temperature

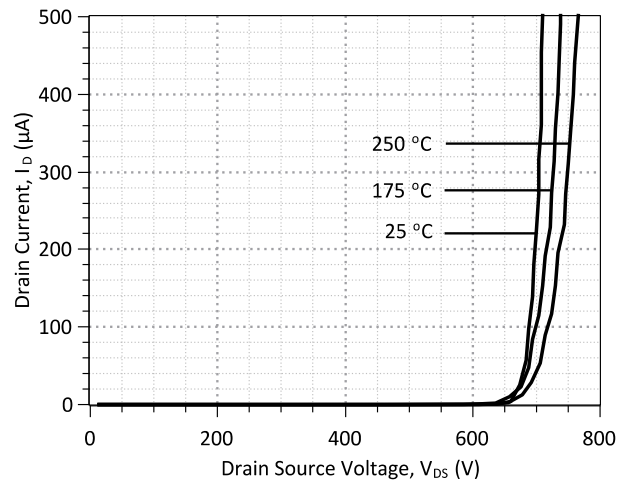


Figure 6: Typical Blocking Characteristics

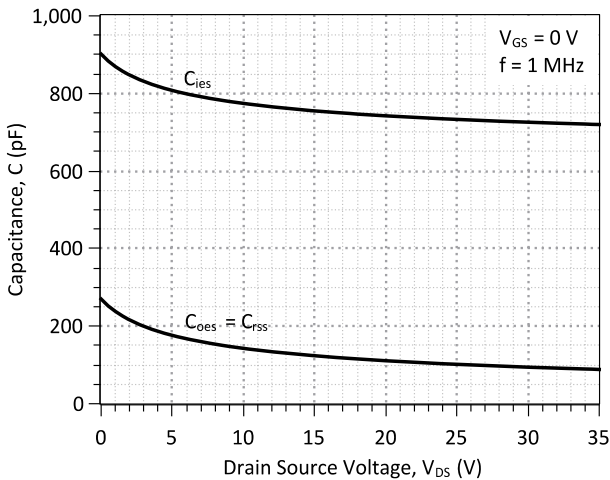


Figure 7: Typical Capacitance vs Drain-Source Voltage

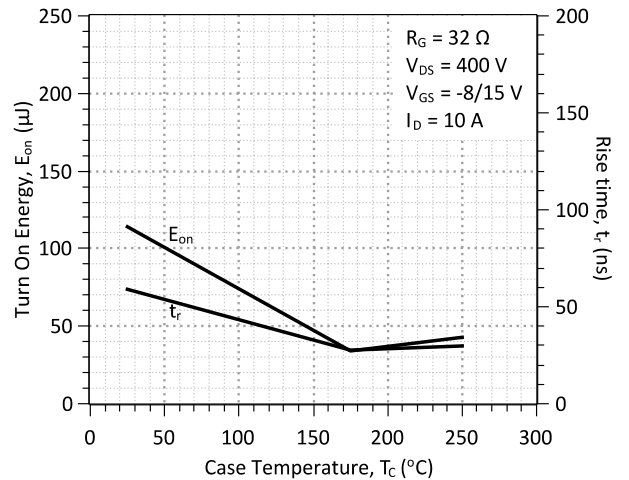


Figure 8: Typical Turn On Energy Losses and Switching Times vs. Temperature

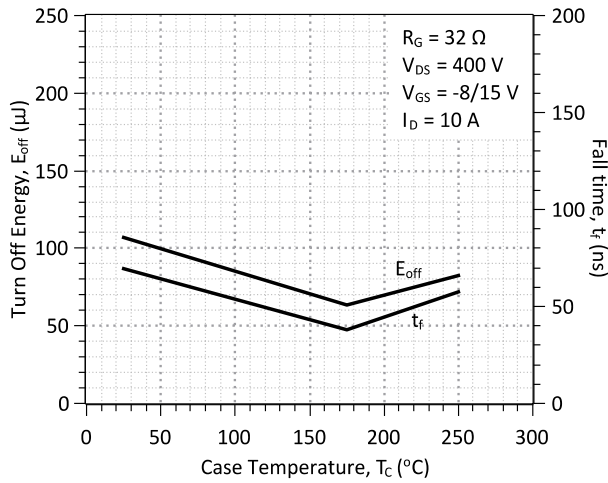


Figure 9: Typical Turn Off Energy Losses and Switching Times vs. Temperature

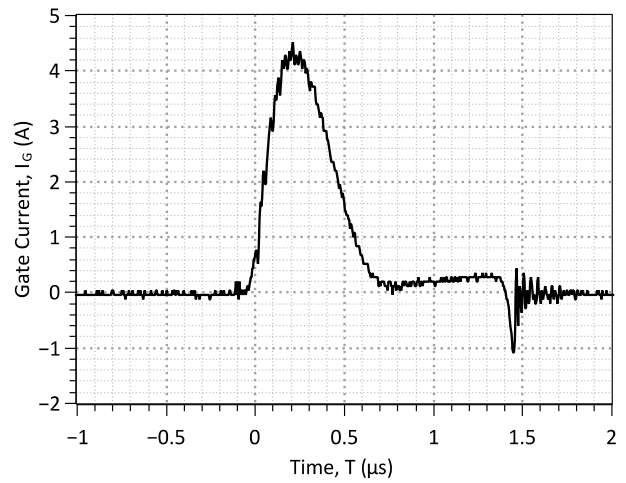
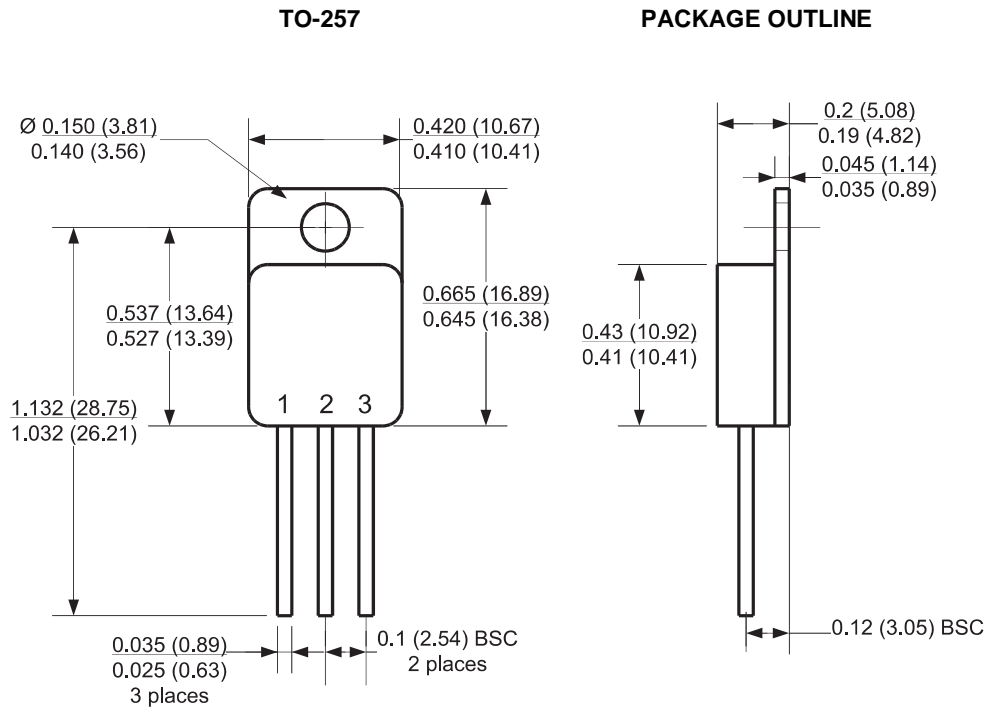


Figure 10: Typical Gate Current Waveform

Package Dimensions:



NOTE
 1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

Revision History

Date	Revision	Comments	Supersedes
2012/08/24	0	Initial release	

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